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Erratum: High current density GaAs/Si rectifying heterojunction by defect free Epitaxial Lateral overgrowth on Tunnel Oxide from nano-seed

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In the original HTML version of this Article, all instances of the orientation [1-10] and [3-11] were incorrectly written as “^{1,2,3,4,5,6,7,8,9,10}” and “^{3,4,5,6,7,8,9,10,11}” respectively. In the original PDF version of this Article, all instances of the orientation [1-10] and [3-11] were given as “¹⁻¹⁰” and “³⁻¹¹” respectively. These errors have now been fixed in the HTML and PDF versions of this Article.



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